



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Features

- $BV_{CEO} > 50V$
- $I_C = 3A$ High Continuous Collector Current
- I_{CM} up to 6A Peak Pulse Current
- 2W Power Dissipation
- Low Saturation Voltage $V_{CE(sat)} < 220mV @ 1A$
- $R_{CE(sat)} = 87m\Omega @ 2.75A$ for a Low Equivalent On-Resistance
- h_{FE} Characterized up to 6A for High Current Gain Hold-Up

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per
MIL-STD-202, Method 208 
- Weight: 0.052 grams (Approximate)

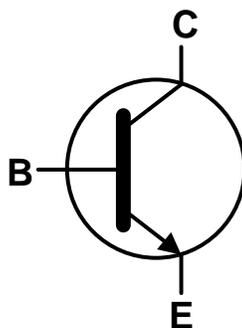
Applications

- Load Management Functions
- Motor Control
- DC-DC / DC-AC Converters

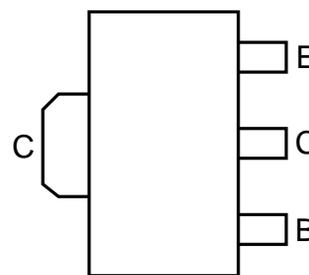


SOT89

Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	3	A
Peak Pulse Current	I _{CM}	6	A
Continuous Base Current	I _B	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

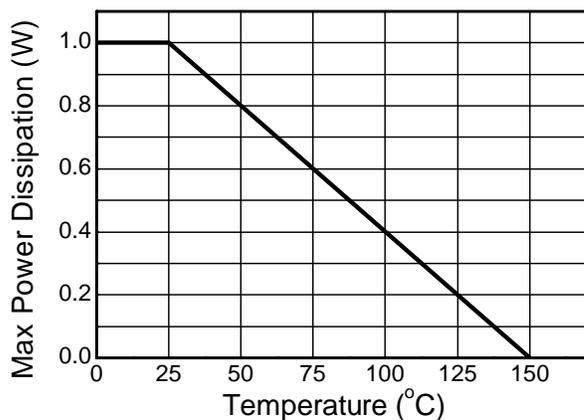
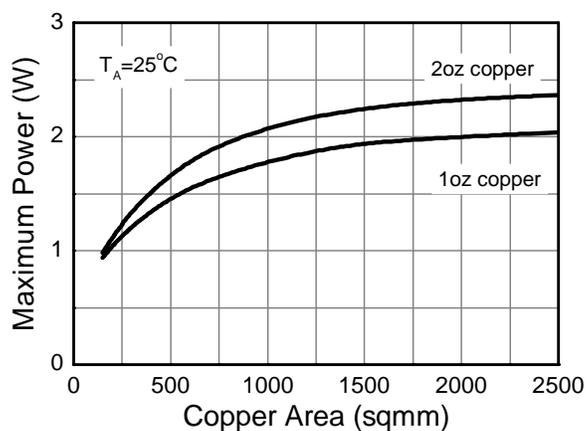
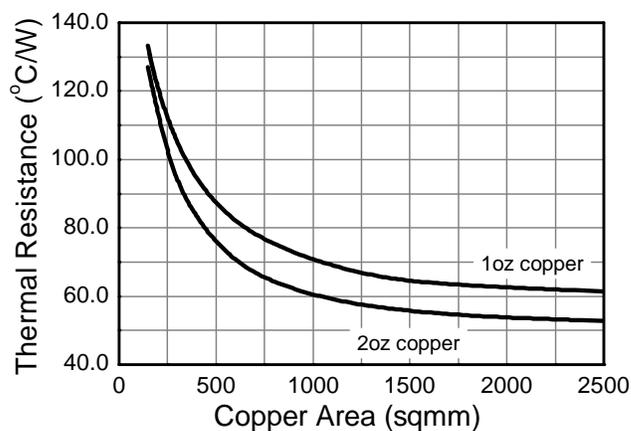
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	(Note 6)	0.7
		(Note 7)	1.0
		(Note 8)	1.5
		(Note 9)	2.0
Thermal Resistance, Junction to Ambient Air	R _{θJA}	(Note 6)	178
		(Note 7)	125
		(Note 8)	83
		(Note 9)	62.5
Thermal Resistance, Junction to Lead	R _{θJL}	6	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 11)

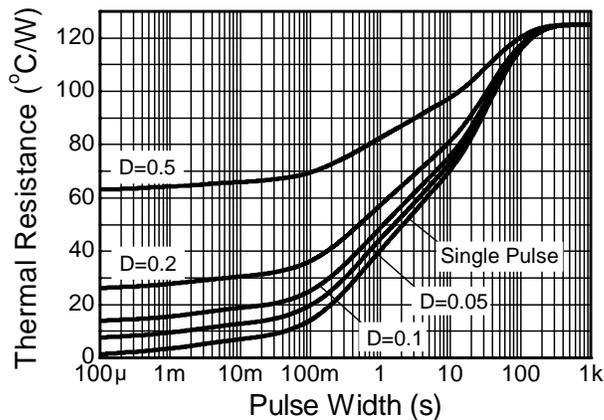
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the exposed collector pad on minimum recommended pad layout (MRP) 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as Note 6, except the device is mounted with the exposed collector pad on 15mm x 15mm 1oz copper.
 8. Same as Note 6, except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.
 9. Same as Note 6, except the device is mounted with the exposed collector pad on 40mm x 40mm 1oz copper.
 10. Thermal resistance from junction to solder-point (on the exposed collector pad).
 11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

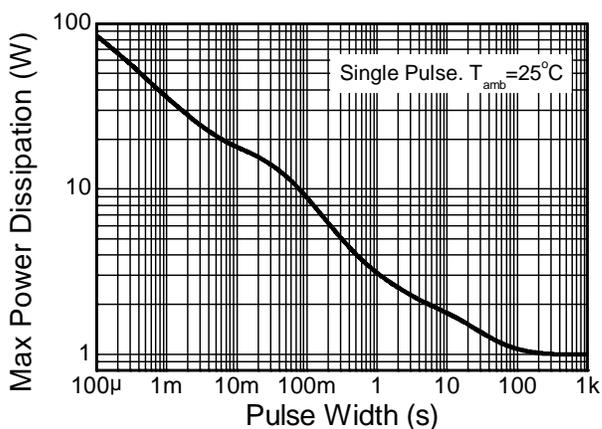
Thermal Characteristics and Derating Information



Derating Curve



Transient Thermal Impedance



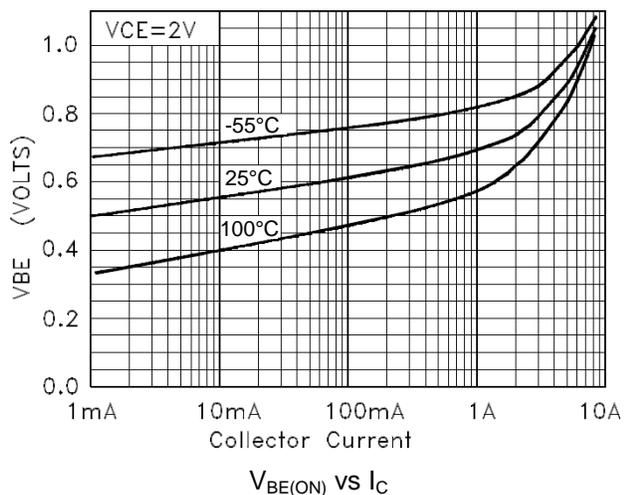
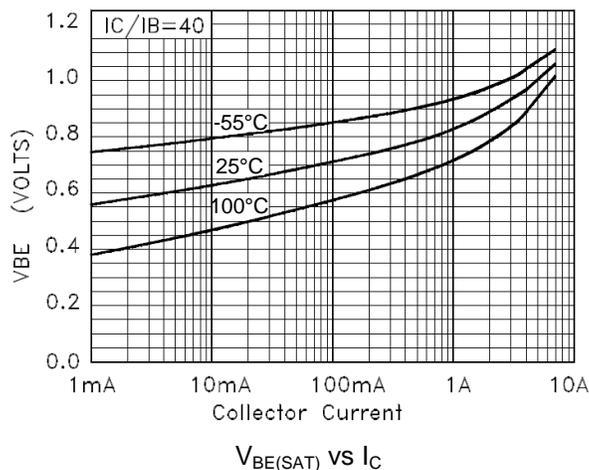
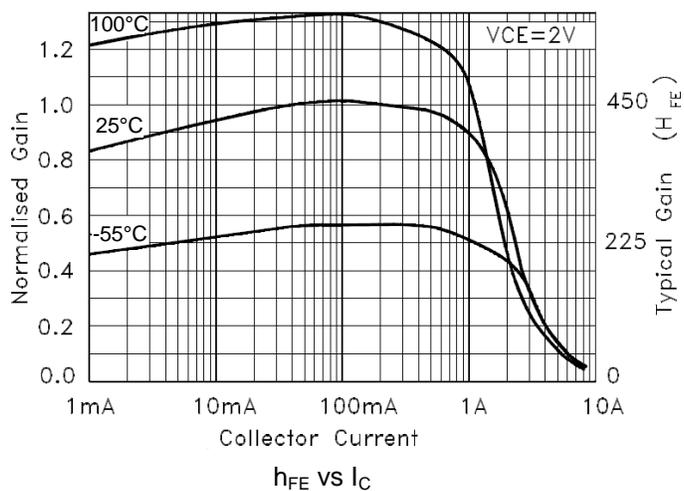
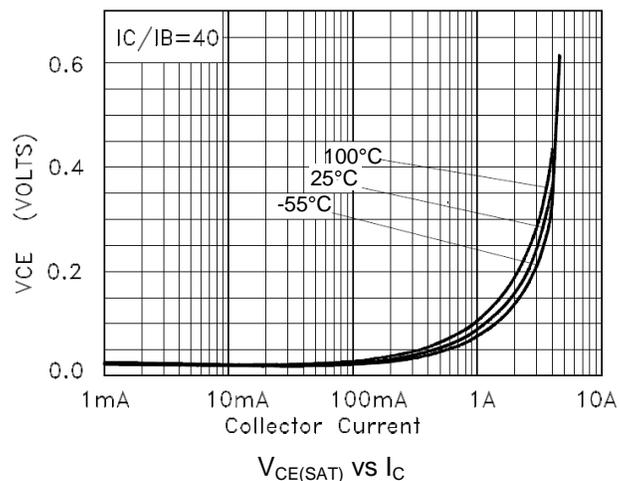
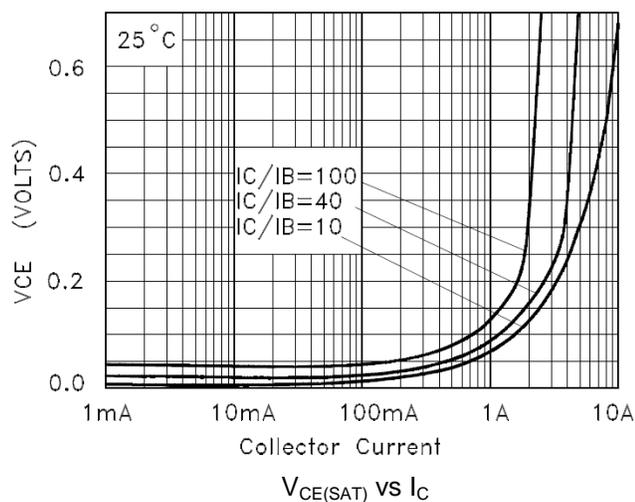
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CB0}	50	190	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	50	65	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	—	V	I _E = 100μA
Collector Cutoff Current	I _{CB0}	—	—	100	nA	V _{CB} = 40V
Emitter Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 5.6V
Emitter Cutoff Current	I _{CES}	—	—	100	nA	V _{CES} = 40V
DC Current Transfer Static Ratio (Note 12)	h _{FE}	200 300 200 100 —	400 450 400 200 30	—	—	I _C = 10mA, V _{CE} = 2V I _C = 200mA, V _{CE} = 2V I _C = 1A, V _{CE} = 2V I _C = 2A, V _{CE} = 2V I _C = 6A, V _{CE} = 2V
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}	—	13 150 190 240	25 220 260 320	mV	I _C = 100mA, I _B = 10mA I _C = 1A, I _B = 10mA I _C = 2A, I _B = 50mA I _C = 2.75A, I _B = 100mA
Base-Emitter Saturation Voltage (Note 12)	V _{BE(sat)}	—	0.97	1.1	V	I _C = 2.75A, I _B = 100mA
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(on)}	—	0.89	1	V	I _C = 2.75A, V _{CE} = 2V
Transitional Frequency	f _T	100	165	—	MHz	I _C = 50mA, V _{CE} = 10V f = 100MHz
Output Capacitance	C _{obo}	—	12	20	pF	V _{CB} = 10V, f = 1MHz,
Turn-On Time	t _(on)	—	170	—	ns	V _{CC} = 10V, I _C = 1A
Turn-Off Time	t _(off)	—	750	—	ns	I _{B1} = 10mA, I _{B2} = -10mA

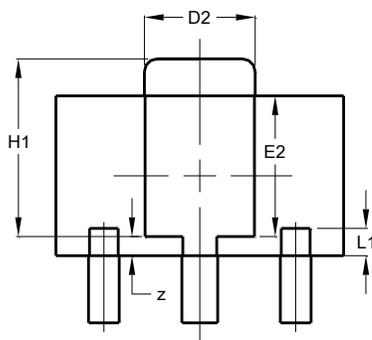
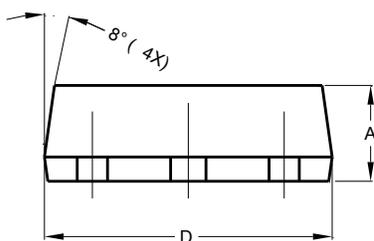
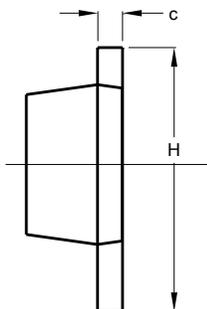
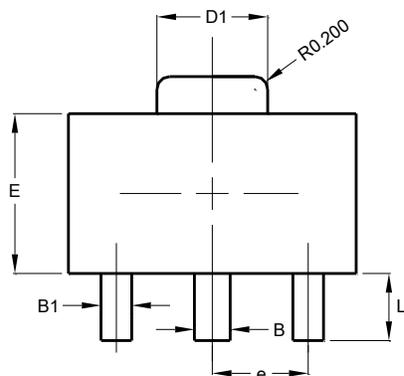
Note: 12. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

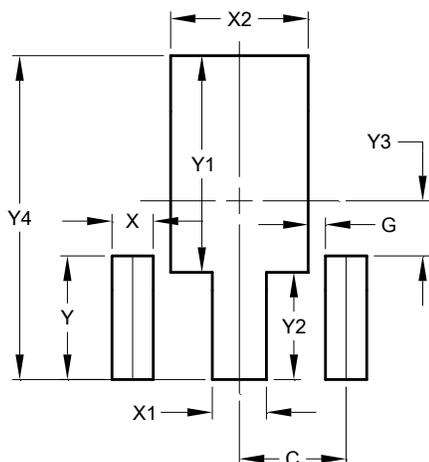
SOT89



SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530